

Silicon NPN Power Transistors

2SC1050

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For use in audio and general purpose applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

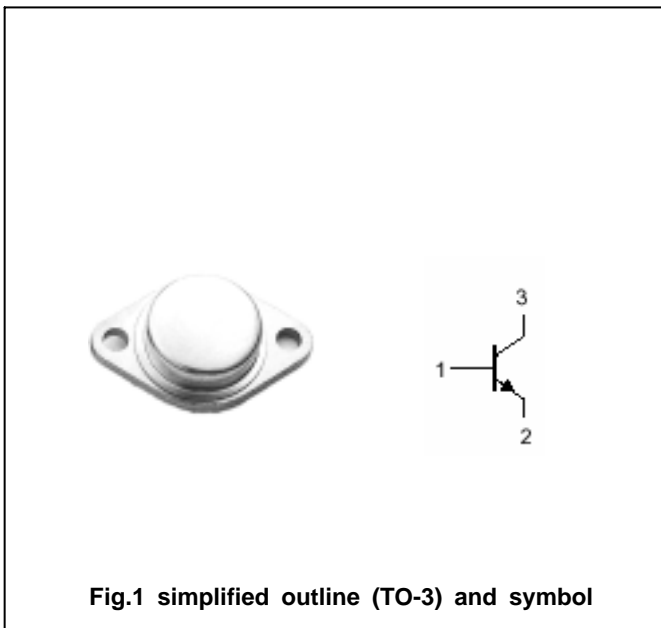


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		1	A
P _T	Total power dissipation	T _{mb} =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	300			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.5A; I _B =0.1A			1.2	V
V _{BEsat}	Base-emitter saturation voltage	I _C =0.5A; I _B =0.1A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =300V; I _E =0			0.1	mA
I _{CEO}	Collector cut-off current	V _{CE} =300V; I _B =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =0.3A ; V _{CE} =5V	30		200	

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PACKAGE OUTLINE

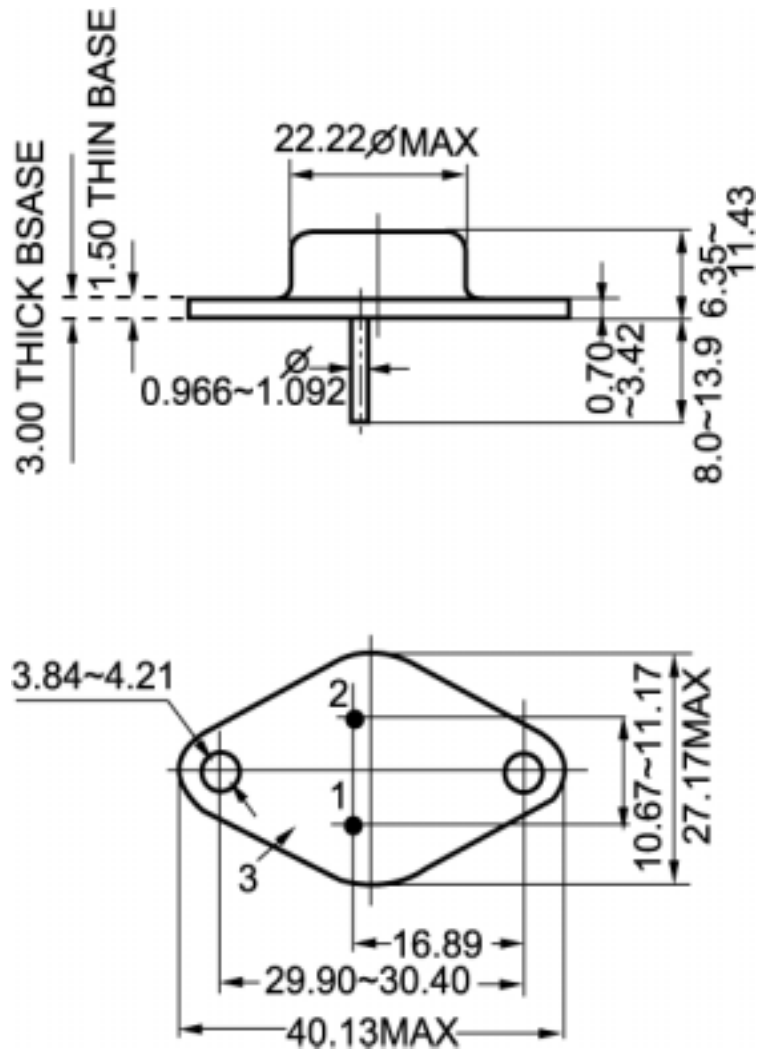


Fig.2 Outline dimensions